

## MMBT5401LT1 TRANSISTOR (PNP)

### FEATURES

Power dissipation

$$P_{CM}: 0.3 \text{ W (Tamb=25°C)}$$

Collector current

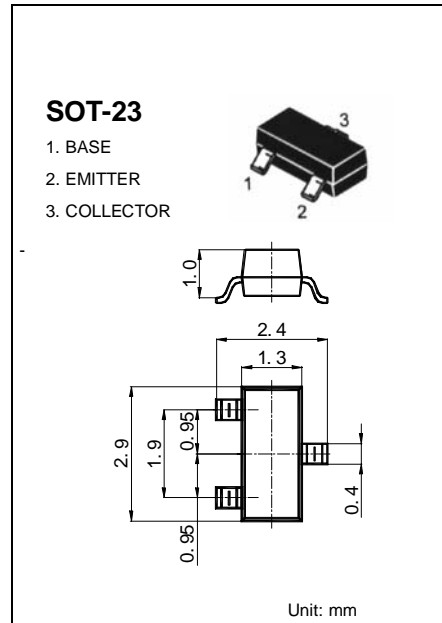
$$I_{CM}: -0.6 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: -160 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55°C \text{ to } +150°C$$



### ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

| Parameter                            | Symbol        | Test conditions                            | MIN  | MAX  | UNIT    |
|--------------------------------------|---------------|--|------|------|---------|
| Collector-base breakdown voltage     | $V_{(BR)CBO}$ | $I_C = -100 \mu A, I_E = 0$                | -160 |      | V       |
| Collector-emitter breakdown voltage  | $V_{(BR)CEO}$ | $I_C = -1 \text{ mA}, I_B = 0$             | -150 |      | V       |
| Emitter-base breakdown voltage       | $V_{(BR)EBO}$ | $I_E = -10 \mu A, I_C = 0$                 | -5   |      | V       |
| Collector cut-off current            | $I_{CBO}$     | $V_{CB} = -120V, I_E = 0$                  |      | -0.1 | $\mu A$ |
| Emitter cut-off current              | $I_{EBO}$     | $V_{EB} = -4V, I_C = 0$                    |      | -0.1 | $\mu A$ |
| DC current gain                      | $H_{FE(1)}$   | $V_{CE} = -5V, I_C = -1mA$                 | 80   |      |         |
|                                      | $H_{FE(2)}$   | $V_{CE} = -5V, I_C = -10mA$                | 100  | 200  |         |
|                                      | $H_{FE(3)}$   | $V_{CE} = -5V, I_C = -50mA$                | 50   |      |         |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C = -50mA, I_B = -5mA$                  |      | -0.5 | V       |
| Base-emitter saturation voltage      | $V_{BE(sat)}$ | $I_C = -50mA, I_B = -5mA$                  |      | -1   | V       |
| Transition frequency                 | $f_T$         | $V_{CE} = -5V, I_C = -10mA$<br>$f = 30MHz$ | 100  |      | MHz     |

### DEVICE MARKING

MMBT5401LT1=2L